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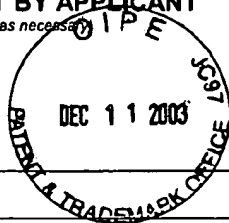
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**INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT**

(Use as many sheets as necessary)



Complete if Known

Application Number	09/256643
Filing Date	February 23, 1999
First Named Inventor	Forbes, Leonard
Group Art Unit	2822
Examiner Name	Trinh, Michael

Sheet 1 of 2

Attorney Docket No: 303.324US2

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Examiner Initials*	Cite No <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>4</sup>
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EXAMINER

Michael Trinh

DATE CONSIDERED

1/22/04

Substitute Disclosure Statement Form (PTO-1449)

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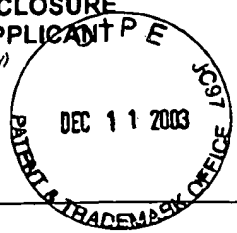
\* No translation, English Abstract only.

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Substitute for form 1449A/PTO <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> (Use as many sheets as necessary)		Complete if Known <b>Application Number</b> 09/256643 <b>Filing Date</b> February 23, 1999 <b>First Named Inventor</b> Forbes, Leonard <b>Group Art Unit</b> 2822 <b>Examiner Name</b> Trinh, Michael	
Sheet 2 of 2		<b>Attorney Docket No:</b> 303.324US2	



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EXAMINER	Michael Trinh	DATE CONSIDERED	1/22/04
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